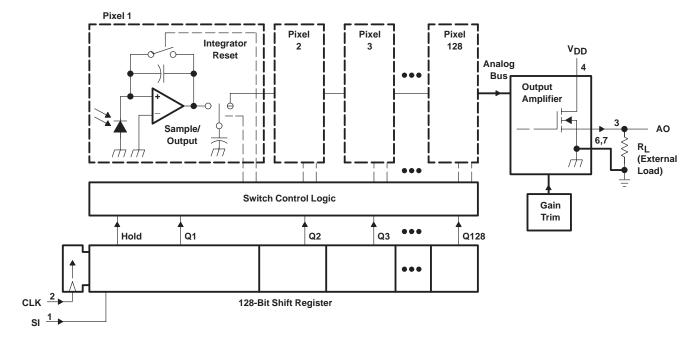
- 128 × 1 Sensor-Element Organization
- 400 Dots-Per-Inch (DPI) Sensor Pitch
- High Linearity and Uniformity for 256 Gray-Scale (8-Bit) Applications
- Output Referenced to Ground
- Low Image Lag . . . 0.5% Typ
- Operation to 2 MHz
- Single 5-V Supply

(TOP VIEW) SI I NC 8 GND CLK [2 7 ΑO 3 6 GND 5 NC 4 V_{DD} NC - No internal connection

description

The TSL1401 linear sensor array consists of a 128×1 array of photodiodes, associated charge amplifier circuitry, and a pixel data-hold function that provides simultaneous-integration start and stop times for all pixels. The pixels measure 63.5 μ m (H) by 55 μ m (W) with 63.5- μ m center-to-center spacing and 8.5- μ m spacing between pixels. Operation is simplified by internal control logic that requires only a serial-input (SI) signal and a clock.

functional block diagram





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



Terminal Functions

TERMINAL		DESCRIPTION				
NAME	NO.	DESCRIPTION				
AO	3	Analog output				
CLK	2	Clock. The clock controls charge transfer, pixel output, and reset.				
GND	6, 7	Ground (substrate). All voltages are referenced to the substrate.				
NC	5, 8	No internal connection				
SI	1	Serial input. SI defines the start of the data-out sequence.				
V _{DD}	4	Supply voltage. Supply voltage for both analog and digital circuits.				

detailed description

The sensor consists of 128 photodiodes arranged in a linear array. Light energy impinging on a photodiode generates photocurrent, which is integrated by the active integration circuitry associated with that pixel.

During the integration period, a sampling capacitor connects to the output of the integrator through an analog switch. The amount of charge accumulated at each pixel is directly proportional to the light intensity and the integration time.

The output and reset of the integrators is controlled by a 128-bit shift register and reset logic. An output cycle is initiated by clocking in a logic 1 on SI. This causes all 128 sampling capacitors to be disconnected from their respective integrators and starts an integrator reset period. As the SI pulse is clocked through the shift register, the charge stored on the sampling capacitors is sequentially connected to a charge-coupled output amplifier that generates a voltage on analog output AO. The integrator reset period ends 18 clock cycles after the SI pulse is clocked in. Then the next integration period begins.

AO is driven by a source follower that requires an external pulldown resistor. When the output is not in the output phase, it is in a high-impedance state. The output is nominally 0 V for no light input and 2 V for a nominal full-scale output.

The TSL1401 is intended for use in a wide variety of applications, including: image scanning, mark and code reading, optical character recognition (OCR) and contact imaging, edge detection and positioning, and optical linear and rotary encoding.



absolute maximum ratings†

Supply voltage, V _{DD}	7 V
Digital input current range, I ₁	–20 mA to 20 mA
Operating free-air temperature range, T _A	0°C to 70°C
Storage temperature range, T _{stq}	–25°C to 85°C
Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

recommended operating conditions (see Figure 1 and Figure 2)

	MIN	NOM	MAX	UNIT
Supply voltage, V _{DD}	4.5	5	5.5	V
Input voltage, V _I	0		V_{DD}	V
High-level input voltage, VIH	$V_{DD} \times 0.7$		V_{DD}	V
Low-level input voltage, V _{IL}	0		$V_{DD} \times 0.3$	V
Wavelength of light source, λ	400		700	nm
Clock frequency, f _{clock}	5		2000	kHz
Sensor integration time, t _{int}	0.0645		100	ms
Setup time, serial input, t _{SU(SI)}	0			ns
Hold time, serial input, th(SI) (see Note 1)	20			ns
Operating free-air temperature, T _A	0		70	°C

NOTE 1: SI must go low before the rising edge of the next clock pulse.

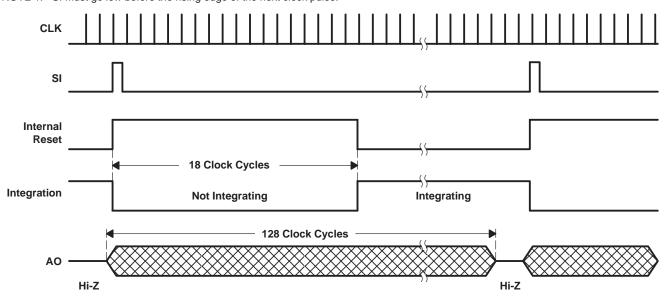


Figure 1. Timing Waveforms

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electrical characteristics at f_{clock} = 200 kHz, V_{DD} = 5 V, T_A = 25°C, λ_p = 565 nm, t_{int} = 5 ms, R_L = 330 Ω , E_e = 14 μ W/cm² (unless otherwise noted) (see Note 2)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Analog output voltage (white, average over 128 pixels)		1.8	2	2.2	V
	Analog output voltage (dark, average over 128 pixels)	$E_e = 0$	0	0.1	0.2	V
PRNU	Pixel response nonuniformity	See Note 3		±4%	± 7.5%	
	Nonlinearity of analog output voltage	See Note 4		±0.4%		FS
	Output noise voltage	See Note 5		1		mVrms
	Saturation exposure		136	175		nJ/cm ²
	Analog output saturation voltage		3	3.5		V
DSNU	Dark signal nonuniformity	All pixels, $E_e = 0$ See Note 6		0.08	0.120	V
		All except pixel 1, E _e = 0 See Note 6		0.017	0.035	
IL	Image lag	See Note 7		0.5%		
I _{DD}	Supply current			2.5	4	mA
ΊΗ	High-level input current	$V_I = V_{DD}$			1	μΑ
I _{IL}	Low-level input current	V _I = 0			1	μΑ
Ci	Input capacitance			5	·	pF

NOTES: 2. Clock duty cycle is assumed to be 50%.

- 3. PRNU is the maximum difference between the voltage from any single pixel and the average output voltage from all pixels of the device under test when the array is uniformly illuminated.
- 4. Nonlinearity is defined as the maximum deviation from a best-fit straight line over the dark-to-white irradiance levels, as a percent of analog output voltage (white).
- 5. RMS noise is the standard deviation of a single-pixel output under constant illumination as observed over a 5-second period.
- 6. DNSU is the difference between the maximum and minimum of dark-current voltage.
- 7. Image lag is a residual signal left in a pixel from a previous exposure. It is defined as a percent of white-level signal remaining after a pixel is exposed to a white condition followed by a dark condition:

$$IL = \frac{V_{AO}^{-V}AO(dark)}{V_{AO(white)} - V_{AO(dark)}} \times 100$$



operating characteristics over recommended ranges of supply voltage and operating free-air temperature (see Figure 2)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t _{w(H)}	Clock pulse duration (high)			50			ns
t _{w(L)}	Clock pulse duration (low)			50			ns
t _S	Analog output settling time to $\pm 1\%$	$R_L = 330 \Omega$,	C _L = 50 pF		350		ns

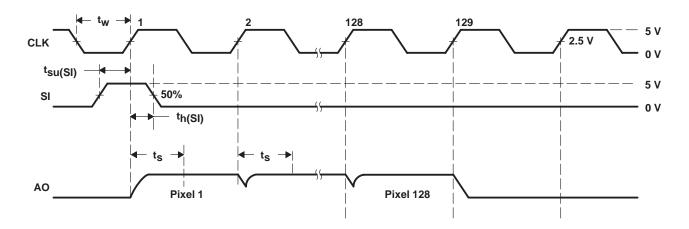


Figure 2. Operational Waveforms

TYPICAL CHARACTERISTICS

PHOTODIODE SPECTRAL RESPONSIVITY

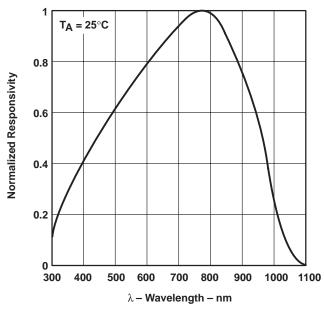
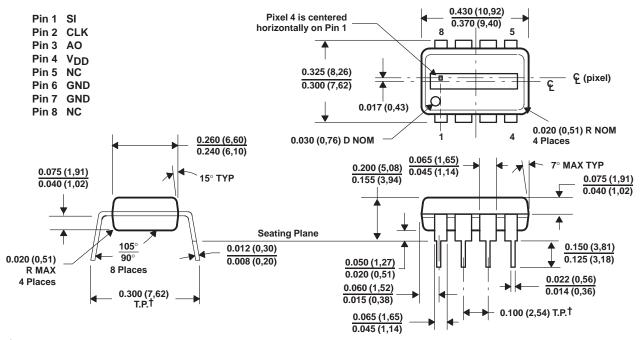


Figure 3



APPLICATIONS INFORMATION

This dual-in-line package consists of a circuit mounted on a lead frame and encapsulated with an electrically nonconductive clear plastic compound.



† True position when unit is installed

NOTES: A. All linear dimensions are in inches and parenthetically in millimeters.

B. This drawing is subject ot change without notice.

Figure 4. Packaging Configuration



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